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TO-220FL Ł N MOS N-CHANNEL MOSFET in a TO-220FL Plastic Package.

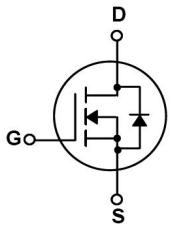
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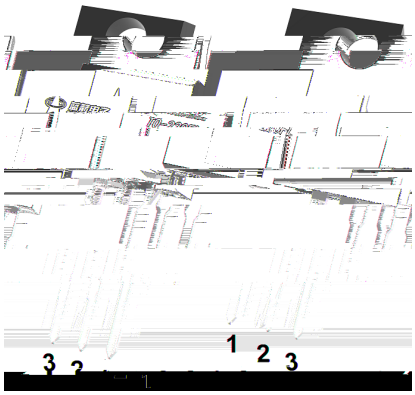
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Ultra low gate charge, low effective output capacitance, high switch speed.

Hט AC/DC

It is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.





PIN1 G PIN 2 D PIN 3 S

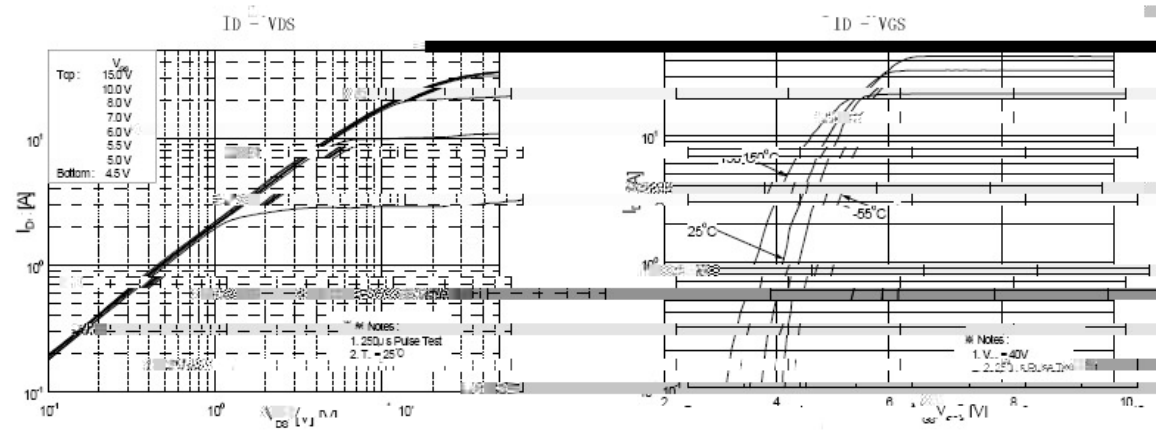
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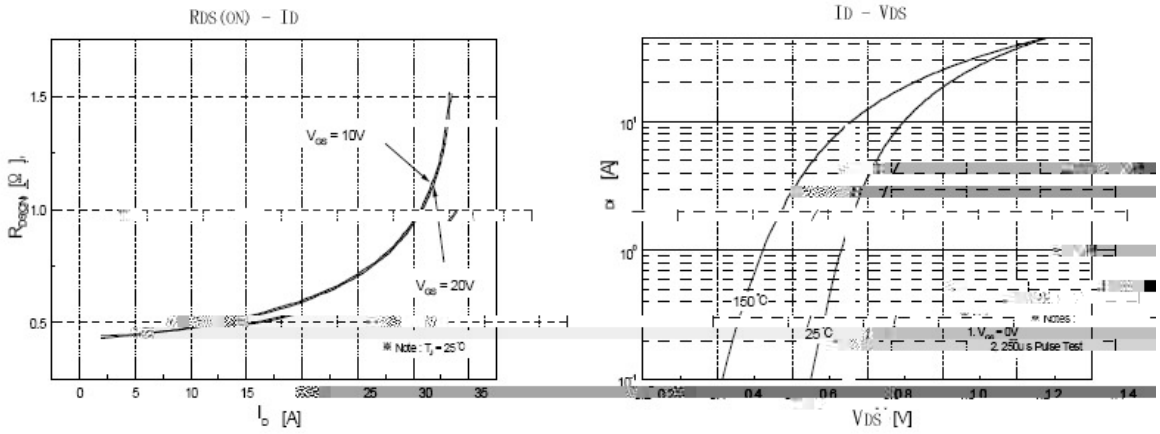
See Marking Instructions.

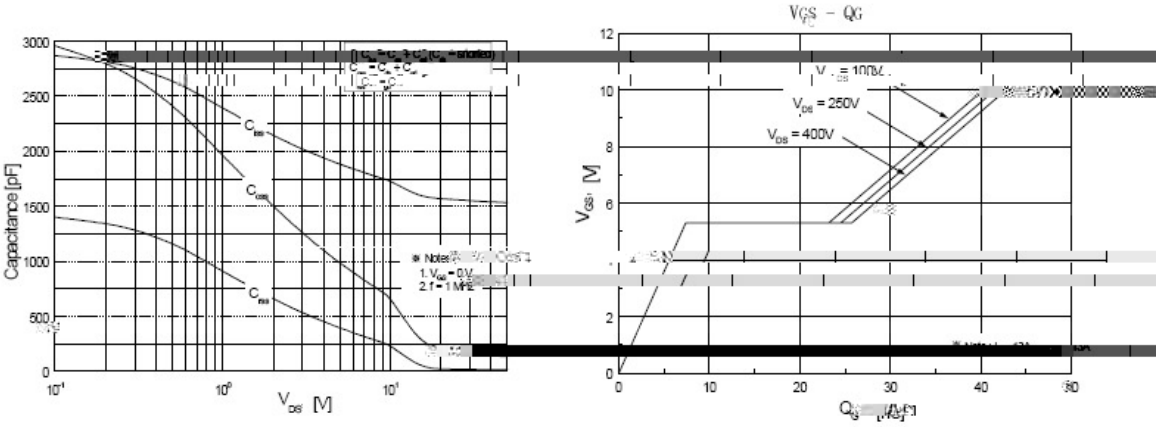
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	500	V
Drain Current	I_D(Tc=25)	13	A
	I_D(Tc=100)	8	A
Drain Current - Pulsed	I_{DM}	52	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	860	mJ
Repetitive Avalanche Energy	E_{AR}	19.5	mJ
Avalanche Current	I_{AR}	13	A
Power Dissipation	P_D(Tc=25)	48	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	500			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=500V V_{GS}=0V			1.0	A
		V_{DS}=400V T_C=125			10	A
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±30V V_{DS}=0V			±0.1	A

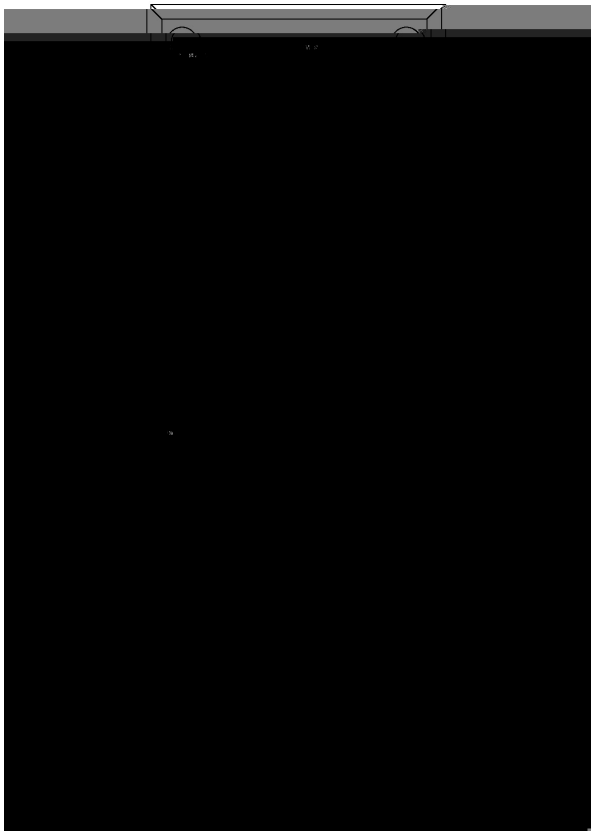
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Top:
Bottom:
* Notes:
1. 250μs Pulse Test
2. T_C = 25°C
150°C
25°C
-55°C
* Notes:
1. V_DS = 40V


RDS(ON) - ID
V_GS = 10V
V_GS = 20V
* Note: T_J = 25°C
I_D [A]
ID - VDS
150°C
25°C
* Notes:
1. V_GS = 0V
2. 250μs Pulse Test
V_DS [V]


Capacitance [pF]
C_iss
C_oss
C_rss
* Notes:
1. V_GS = 0V
2. f = 1MHz
V_DS [V]
VGS - QG
V_DS = 250V
V_DS = 400V
V_GS [V]

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13N50

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Note:

BR:	Company Code
13N50:	Product Type
****:	Lot No. Code, code change with Lot No